优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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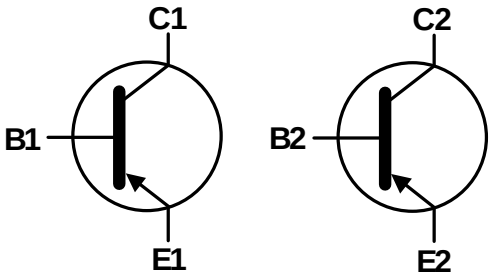
Features

- BV_{CEO} > -60V
- I_{CM} = -1A Peak Pulse Current
- General Purpose PNP Transistors Ideally Suited for Low Power Amplification and Switching Applications
- Dual Transistors in a Single SOT26 Package, Taking Half of the Footprint of Two Equivalent Transistors in SOT23
- Epitaxial Planar Die Construction

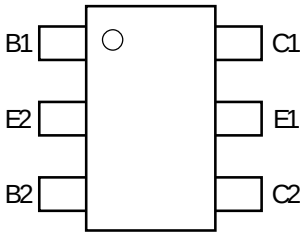
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.015 grams (Approximate)

Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-600	mA
Peak Pulsed Collector Current	I_{CM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

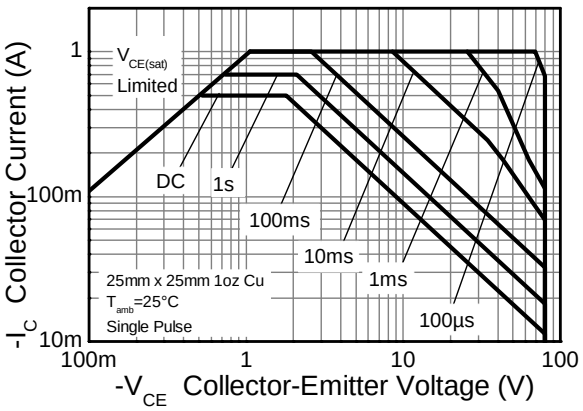
Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Notes 6 & 7)	P_D	1.28 10.3	W mW/°C
	(Notes 5 & 7)		0.90 7.14	
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	97	°C/W
	(Notes 5 & 7)		140	
Thermal Resistance, Junction to Lead	(Note 8)	$R_{\theta JL}$	113	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 9)

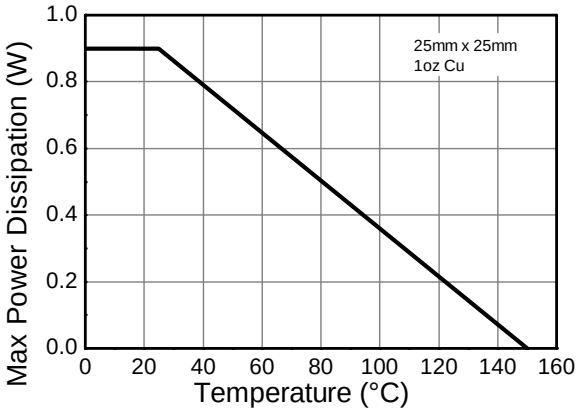
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

Notes:
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. Same as Note 5, except the device is measured at $t \leq 5$ seconds.
7. For a dual device with one active die.
8. Thermal resistance from junction to solder-point (at the end of the collector lead).
9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

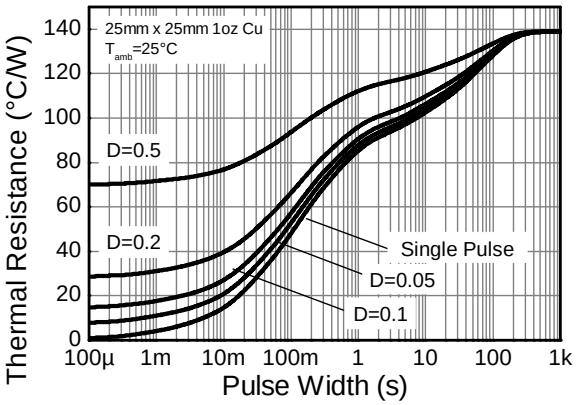
Thermal Characteristics and Derating Information



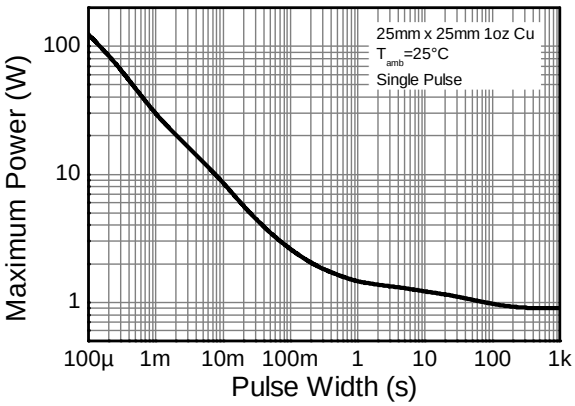
Safe Operating Area



Derating Curve



Transient Thermal Impedance



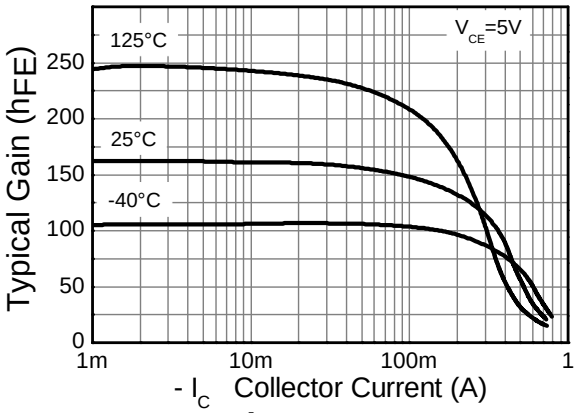
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

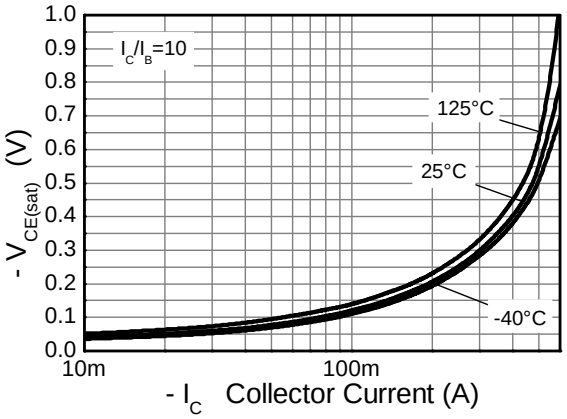
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-60	—	—	V	I_C = -10μA, I_E = 0
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	-60	—	—	V	I_C = -10mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	—	—	V	I_E = -10μA, I_C = 0
Collector-Base Cut-Off Current	I_{CBO}	—	—	-10	nA	V_{CB} = -50V, I_E = 0
		—	—	-10	μA	V_{CB} = -50V, I_E = 0, T_A = +150°C
Collector-Emitter Cut-Off Current	I_{CEV}	—	—	±50	nA	V_{CE} = -30V, V_{BE} = ±0.25V
Base-Emitter Cut-Off Current	I_{BEV}	—	—	±50	nA	V_{CE} = -30V, V_{BE} = ±0.25V
ON CHARACTERISTICS (Note 10)						
DC Current Gain	h_{FE}	75	—	—	—	I_C = -100μA, V_{CE} = -10V
		100	—	—		I_C = -1.0mA, V_{CE} = -10V
		100	—	—		I_C = -10mA, V_{CE} = -10V
		100	—	300		I_C = -150mA, V_{CE} = -10V
		50	—	—		I_C = -500mA, V_{CE} = -10V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	-0.4	V	I_C = -150mA, I_B = -15mA
		—	—	-1.6		I_C = -500mA, I_B = -50mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	—	—	-1.3	V	I_C = -150mA, I_B = -15mA
		—	—	-2.6		I_C = -500mA, I_B = -50mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{obo}	—	5.2	—	pF	V_{CB} = -10V, f = 1.0MHz, I_E = 0mA
Input Capacitance	C_{ibo}	—	16.3	—	pF	V_{EB} = -2.0V, f = 1.0MHz, I_C = 0mA
Current Gain-Bandwidth Product	f_T	200	307	—	MHz	V_{CE} = -2V, I_C = -10mA, f = 100MHz
Turn-On Time	t_{on}	—	—	21	ns	V_{CC} = -30V I_C = -150mA, I_{B1} = -15mA
Delay Time	t_d	—	—	5.5	ns	
Rise Time	t_r	—	—	15.3	ns	
Turn-Off Time	t_{off}	—	—	200	ns	V_{CC} = -6V I_C = -150mA, I_{B1} = I_{B2} = -15mA
Storage Time	t_s	—	—	160	ns	
Fall Time	t_f	—	—	40	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

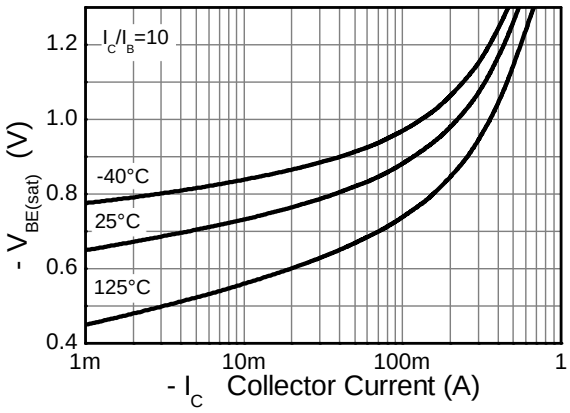
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



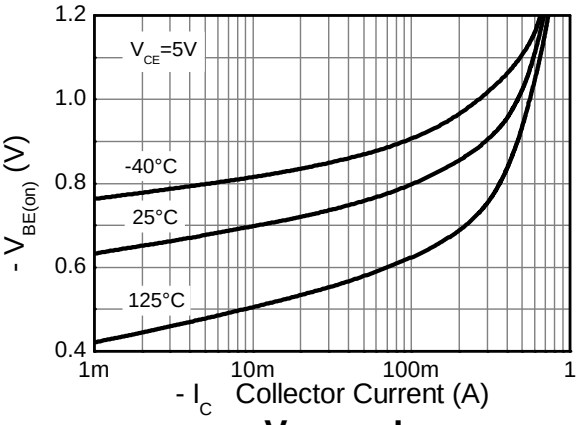
h_{FE} v I_C



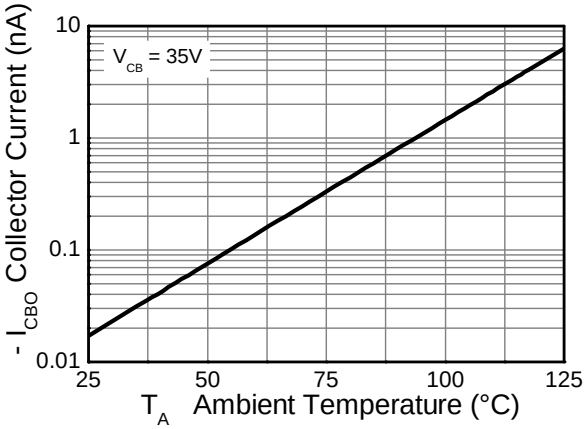
$V_{CE(sat)}$ v I_C



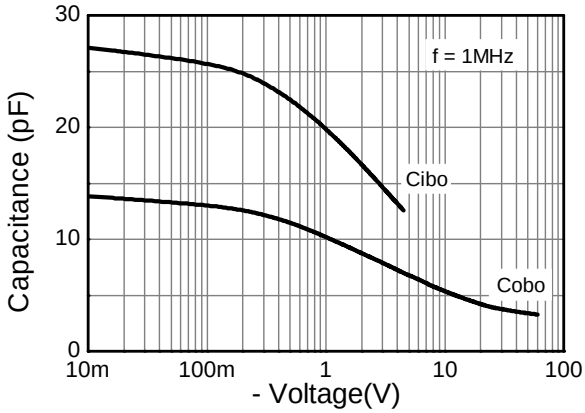
$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



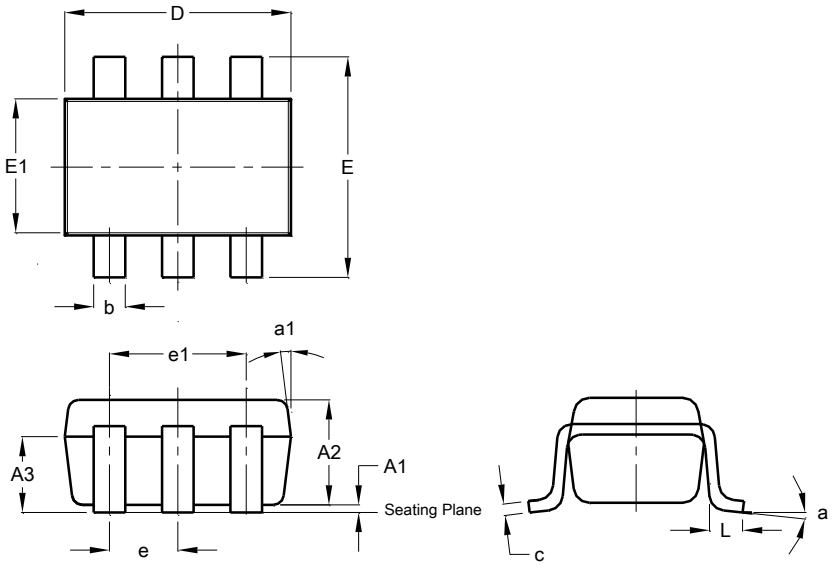
I_{CBO} v T_A



Capacitance v Voltage

Package Outline Dimensions

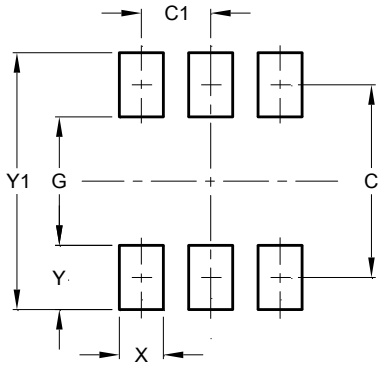
SOT26



SOT26			
Dim	**Min**	**Max**	**Typ**
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	–	–	0.95
e1	–	–	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	–	–	8°
a1	–	–	7°
All Dimensions in mm			

Suggested Pad Layout

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20